REMARKS/ARGUMENTS

Reconsideration of the application is requested.

Claims 1-2 remain in the application. Claim 1 has been amended.

In the section entitled "Claim Rejections - 35 USC § 103" on pages 2-5 of the above-mentioned Office action, claims 1-2 have been rejected as being unpatentable over applicant's admitted prior art (AAPA) in view of Li et al. (US Pat. No. 6,627,530) under 35 U.S.C. § 103(a).

As will be explained below, it is believed that the claims were patentable over the cited art in their original form and the claims have, therefore, not been amended to overcome the references. However, the language of claim 1 has been amended in an effort to even more clearly define the invention of the instant application. Amended claim 1 specifically clarifies the spatial allocation of the third line plane with the write selection lines therein and of the fourth line plane with the write selection lines therein to the first and second line planes, respectively, and the electromagnetic association with the MRAM memory cells in the memory cell plane.

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Before discussing the prior art in detail, it is believed that a brief review of the invention as claimed, would be helpful.

Claim 1 calls for, inter alia:

impressing a main write current in a direction through one of the write selection lines in the third line plane and through one of the write selection lines in the fourth line plane for writing to a particular one of the MRAM cells, while also impressing an additional write current through one of the first selection lines adjoining the particular one of MRAM memory cells and through one of the second selection lines adjoining the particular one of MRAM memory cells; and

when impressing the additional write current, impressing the additional write current being small compared to the main write current and in the same direction as the main write current in the write selection line in the respectively contiguous third and fourth line plane.

The state of the art illustrated in Fig. 2 and described in the introductory part of the specification of the instant application can be found, for example, in EP-A-1061592.

According to the International Preliminary Examination Report, this state of the art is neither relevant with regard to anticipation nor obviousness of the invention of the instant application.

Applicant believes that the obviousness rejection of claims 1-2 of the instant application by the Examiner in view of a combination of the above-mentioned EP-A-1061592 with Li et al., is not justified, because Li et al. describe neither a

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MRAM memory structure with additional third and fourth line planes, nor the writing process specified in claim 1 of the instant application.

Li et al. describe a method for fabricating a threedimensional structure formed of memory cells which can be activated by selection lines which are stacked on top of each other and which cross each other (see Fig. 8). For example, the memory cells disposed in the second-lowest plane are selected by selection lines 126A, 126B which are disposed immediately therebelow and which are in contact with the memory cells and by selection lines 146A, 146B which are disposed above these memory cells and at 90° in relation to the selection lines 126A, 126B. The same configuration and the same selection scheme repeat four times in Fig. 8 in the y-direction. Li et al. do not disclose anywhere that additional write currents can be impressed in additional selection lines which are disposed therebelow and thereabove (for example in the selection lines 106A, 106B below and the selection lines 166A and 166B above) for the purpose of writing memory cells in a certain cell plane. Instead, the memory ells in each memory cell plane are chosen by selection lines which are in contact with these memory cells, for example during the writing of the memory cells. The problem that leakage currents can also flow through the adjacent

memory cells is not mentioned in Li et al. at all. Li et al., even in connection with the state of the art described in the instant application, for example EP-A-1061592, do not provide a person skilled in the art any suggestion how he or she could achieve the object of the invention of the instant application.

It is accordingly believed to be clear that none of the references, whether taken alone or in any combination, either show or suggest the features of claim 1. Claim 1 is, therefore, believed to be patentable over the art and since claim 2 is dependent on claim 1, it is believed to be patentable as well.

In view of the foregoing, reconsideration and allowance of claims 1-2 are solicited.

In the event the Examiner should still find any of the claims to be unpatentable, counsel would appreciate a telephone call so that, if possible, patentable language can be worked out.

If an extension of time for this paper is required, petition for extension is herewith made. Please charge any fees which might be due with respect to 37 CFR Sections 1.16 and 1.17 to

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the Deposit Account of Lerner and Greenberg, P.A., No. 12-1099.

Respectfully submitted,

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